

MC74LVX540

Octal Bus Buffer

Inverting

The MC74LVX540 is an advanced high speed CMOS inverting octal bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74LVX540 features inputs and outputs on opposite sides of the package and two AND-ed active-low output enables. When either $\overline{OE1}$ or $\overline{OE2}$ are high, the terminal outputs are in the high impedance state.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

- High Speed: $t_{PD} = 5.0$ ns (Typ) at $V_{CC} = 3.3$ V
- Low Power Dissipation: $I_{CC} = 4$ μ A (Max) at $T_A = 25^\circ\text{C}$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 3.6 V Operating Range
- Low Noise: $V_{OLP} = 1.2$ V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 124 FETs or 31 Equivalent Gates



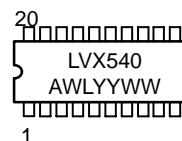
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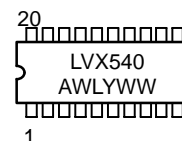
MARKING DIAGRAMS



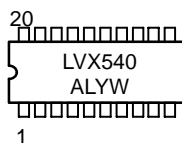
SOIC-20
DW SUFFIX
CASE 751D



TSSOP-20
DT SUFFIX
CASE 948E



SOIC EIAJ-20
M SUFFIX
CASE 967



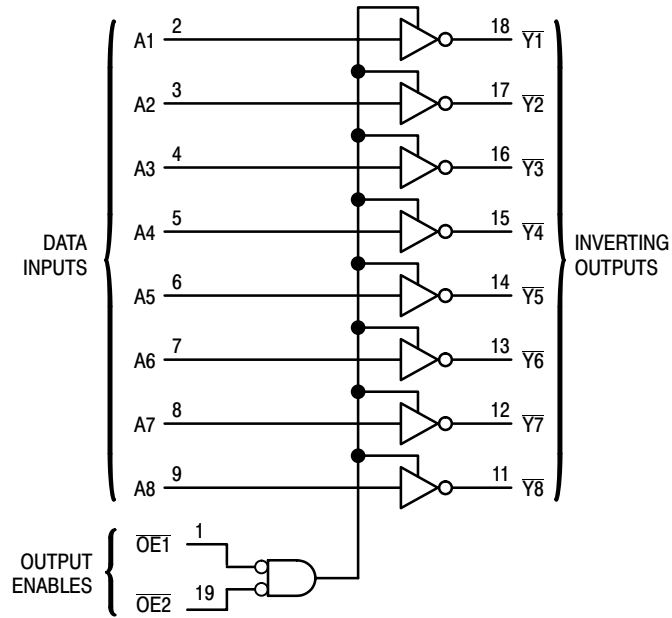
A = Assembly Location
L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74LVX540M	SOIC EIAJ-20	40 Units/Rail
MC74LVX540MEL	SOIC EIAJ-20	2000 Units/Reel

MC74LVX540

LOGIC DIAGRAM



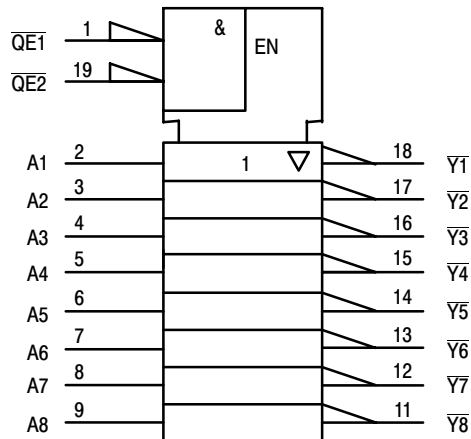
PIN ASSIGNMENT

OE1	1	20	V _{CC}
A1	2	19	OE2
A2	3	18	Y1
A3	4	17	Y2
A4	5	16	Y3
A5	6	15	Y4
A6	7	14	Y5
A7	8	13	Y6
A8	9	12	Y7
GND	10	11	Y8

FUNCTION TABLE

Inputs			Output Y
OE1	OE2	A	
L	L	L	H
L	L	H	L
H	X	X	Z
X	H	X	Z

IEC LOGIC DIAGRAM



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MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	– 0.5 to + 7.0	V
V_{in}	DC Input Voltage	– 0.5 to + 7.0	V
V_{out}	DC Output Voltage	– 0.5 to $V_{CC} + 0.5$	V
I_{IK}	Input Diode Current	–20	mA
I_{OK}	Output Diode Current	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 75	mA
P_D	Power Dissipation in Still Air, SOIC Packages† TSSOP Package†	500 450	mW
T_{stg}	Storage Temperature	– 65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

†Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C
TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage	2.0	3.6	V
V_{in}	DC Input Voltage	0	5.5	V
V_{out}	DC Output Voltage	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	–40	+85	°C
t_r, t_f	Input Rise and Fall Time $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ (See Figure 1)	0	100	ns/V

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DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} V	T _A = 25°C			T _A = – 40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 3.6	1.50 2.0 2.4			1.50 2.0 2.4		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 3.6			0.50 0.80 0.80		0.50 0.80 0.80	V
V _{OH}	Minimum High-Level Output Voltage V _{in} = V _{IH} or V _{IL}	I _{OH} = – 50 µA I _{OH} = – 50 µA I _{OH} = – 4 mA	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V _{OL}	Maximum Low-Level Output Voltage V _{in} = V _{IH} or V _{IL}	I _{OL} = 50 µA I _{OL} = 50 µA I _{OL} = 4 mA	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
I _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 3.6			± 0.1		± 1.0	µA
I _{OZ}	Maximum Three-State Leakage Current	V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GND	3.6			± 0.25		± 2.5	µA
I _{CC}	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	3.6			4.0		40.0	µA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0 ns)

Symbol	Parameter	Test Conditions	T _A = 25°C			T _A = – 40 to 85°C		Unit
			Min	Typ	Max	Min	Max	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to \bar{Y} (Figures 1 and 3)	V _{CC} = 2.7 V C _L = 15 pF C _L = 50 pF		6.2 8.5	11.3 14.9	1.0 1.0	13.5 17.0	ns
		V _{CC} = 3.3 ± 0.3 V C _L = 15 pF C _L = 50 pF		5.0 6.8	7.0 10.5	1.0 1.0	8.5 12.0	
t _{PZL} , t _{PZH}	Output Enable Time, OE \bar{n} to \bar{Y} (Figures 2 and 4)	V _{CC} = 2.7 V C _L = 15 pF R _L = 1 kΩ C _L = 50 pF		9.5 11.2	13.8 17.3	1.0 1.0	16.5 20.0	ns
		V _{CC} = 3.3 ± 0.3 V C _L = 15 pF R _L = 1 kΩ C _L = 50 pF		7.0 8.8	10.5 14.0	1.0 1.0	12.5 16.0	
t _{PLZ} , t _{PHZ}	Output Disable Time, OE \bar{n} to \bar{Y} (Figures 2 and 4)	V _{CC} = 2.7 V C _L = 50 pF R _L = 1 kΩ		9.8	17.9	1.0	20.0	ns
		V _{CC} = 3.3 ± 0.3 V C _L = 50 pF R _L = 1 kΩ		8.7	15.4	1.0	17.5	
t _{OSLH} , t _{OSHL}	Output to Output Skew	V _{CC} = 2.7 V C _L = 50 pF (Note 1)			1.5		1.5	ns
		V _{CC} = 3.3 ± 0.3 V C _L = 50 pF (Note 1)			1.5		1.5	ns
C _{in}	Maximum Input Capacitance			4	10		10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High Impedance State)			6				pF

C _{PD}	Power Dissipation Capacitance (Note 2)	Typical @ 25°C, V _{CC} = 5.0 V	pF
		17	

- Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} – t_{PLHn}|, t_{OSHL} = |t_{PHLm} – t_{PHLn}|.
- C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per bit). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

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NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 3.3$ V)

Symbol	Parameter	$T_A = 25^\circ\text{C}$		Unit
		Typ	Max	
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.5	0.8	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	-0.5	-0.8	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

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SWITCHING WAVEFORMS

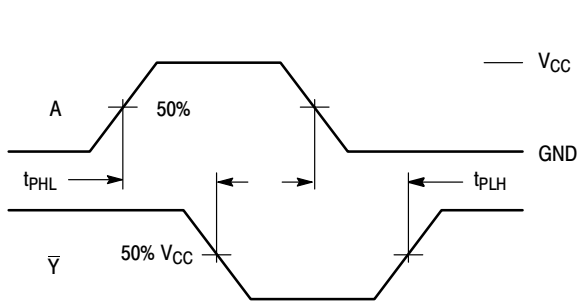


Figure 1.

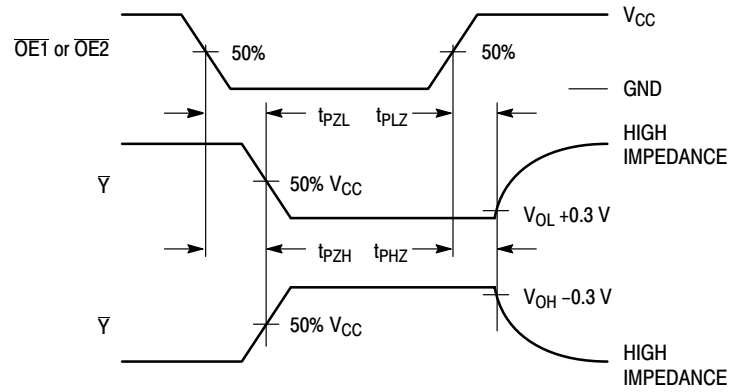
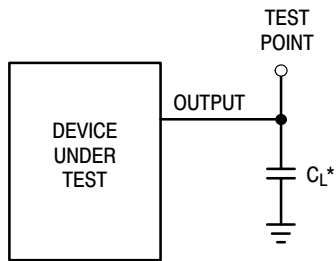


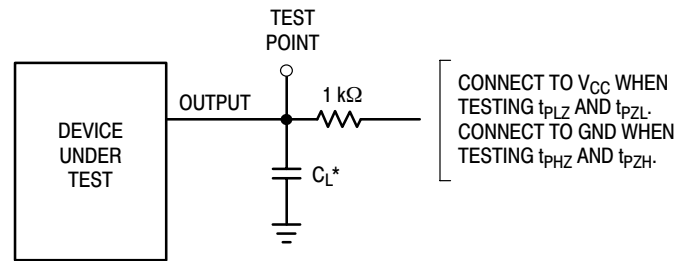
Figure 2.

TEST CIRCUITS



*Includes all probe and jig capacitance

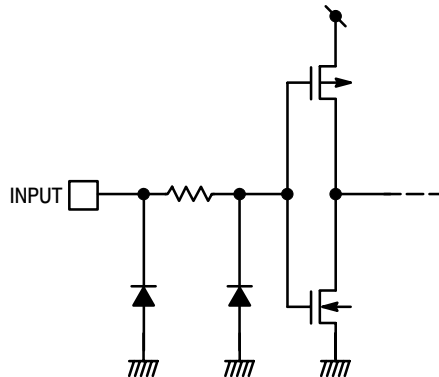
Figure 3.



*Includes all probe and jig capacitance

Figure 4.

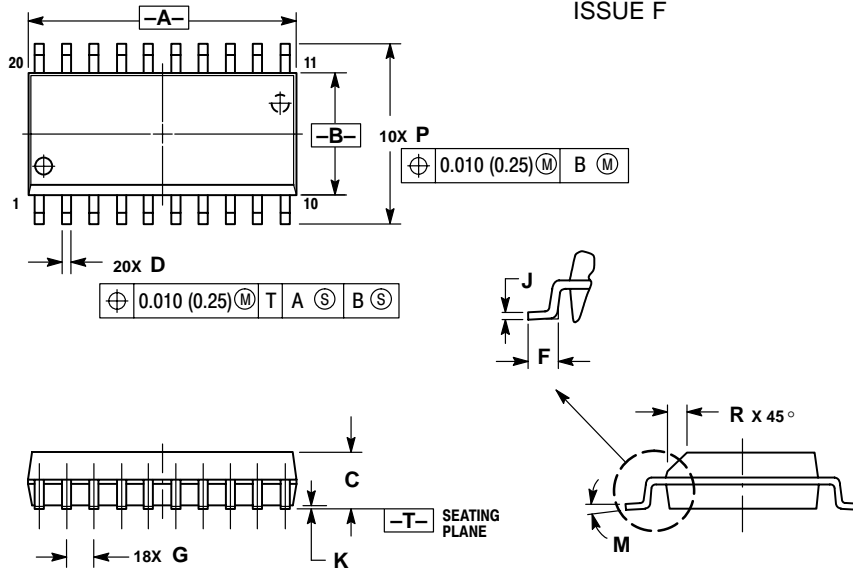
INPUT EQUIVALENT CIRCUIT



MC74LVX540

PACKAGE DIMENSIONS

SOIC-20 DW SUFFIX PLASTIC SOIC WIDE PACKAGE CASE 751D-05 ISSUE F

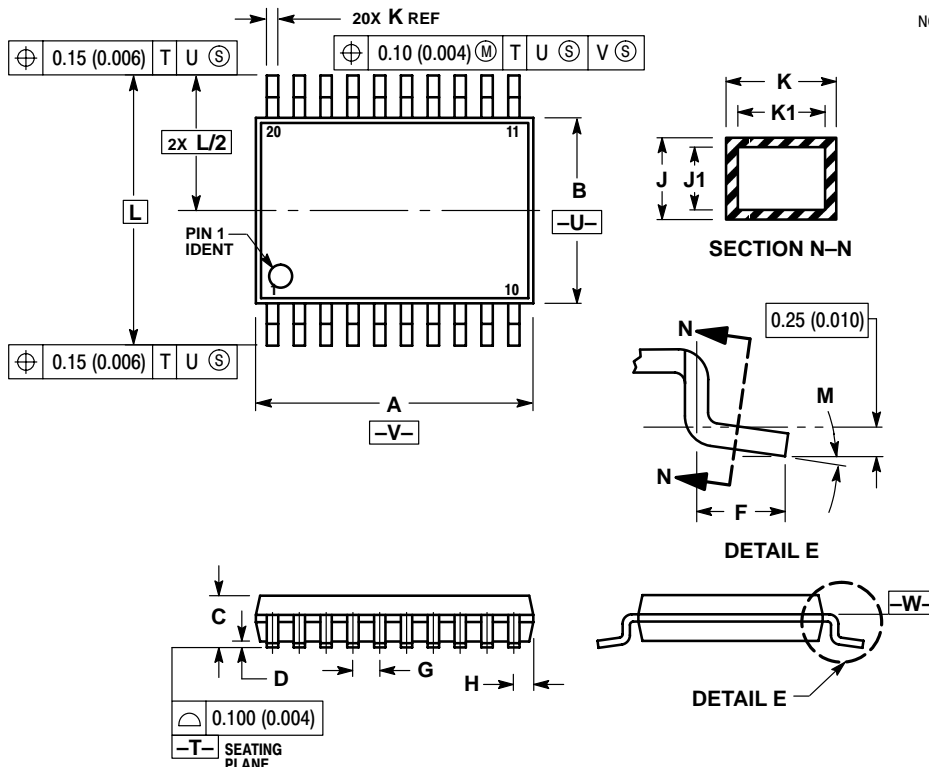


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.150 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.13 (0.005) TOTAL IN EXCESS OF D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	12.65	12.95	0.499	0.510
B	7.40	7.60	0.292	0.299
C	2.35	2.65	0.093	0.104
D	0.35	0.49	0.014	0.019
F	0.50	0.90	0.020	0.035
G	1.27 BSC		0.050 BSC	
J	0.25	0.32	0.010	0.012
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	10.05	10.55	0.395	0.415
R	0.25	0.75	0.010	0.029

TSSOP-20 DT SUFFIX PLASTIC TSSOP PACKAGE CASE 948E-02 ISSUE A



NOTES:

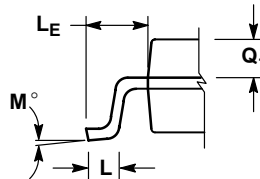
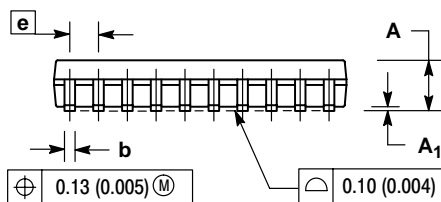
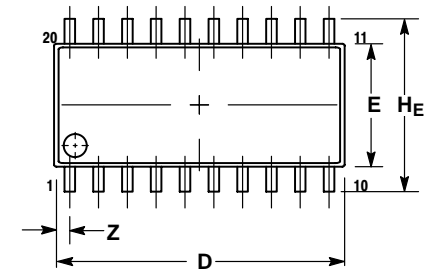
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

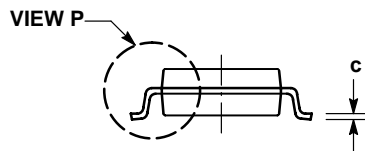
MC74LVX540

PACKAGE DIMENSIONS

SOIC EIAJ-20
M SUFFIX
PLASTIC SOIC EIAJ PACKAGE
CASE 967-01
ISSUE O




DETAIL P



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H _E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L _E	1.10	1.50	0.043	0.059
M	0°	10°	0°	10°
Q ₁	0.70	0.90	0.028	0.035
Z	---	0.81	---	0.032

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